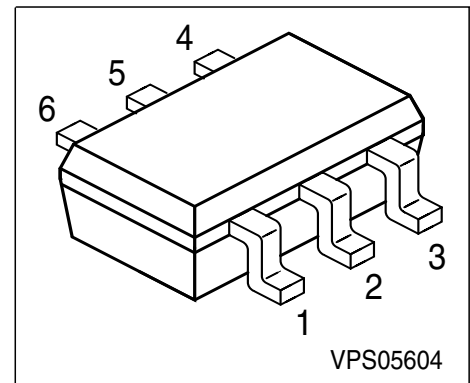
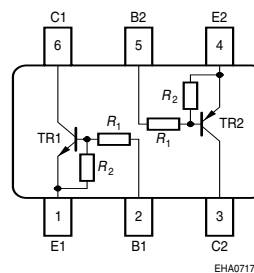
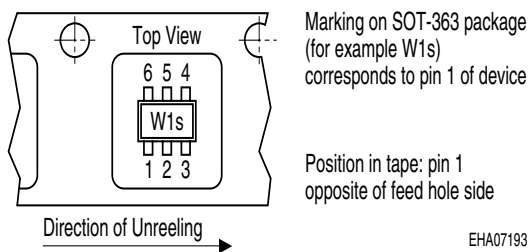


**NPN/PNP Silicon Digital Transistor Array**

- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor ( $R_1=4.7k\Omega$ ,  $R_2=4.7k\Omega$ )



**Tape loading orientation**



Type	Marking	Pin Configuration					Package	
BCR15PN	WAs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	10	
Input on Voltage	$V_{i(on)}$	15	
DC collector current	$I_C$	100	mA
Total power dissipation, $T_S = 115\text{ }^\circ\text{C}$	$P_{tot}$	250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 140$	K/W
--	------------	------------	-----

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A=25^\circ\text{C}$ , unless otherwise specified

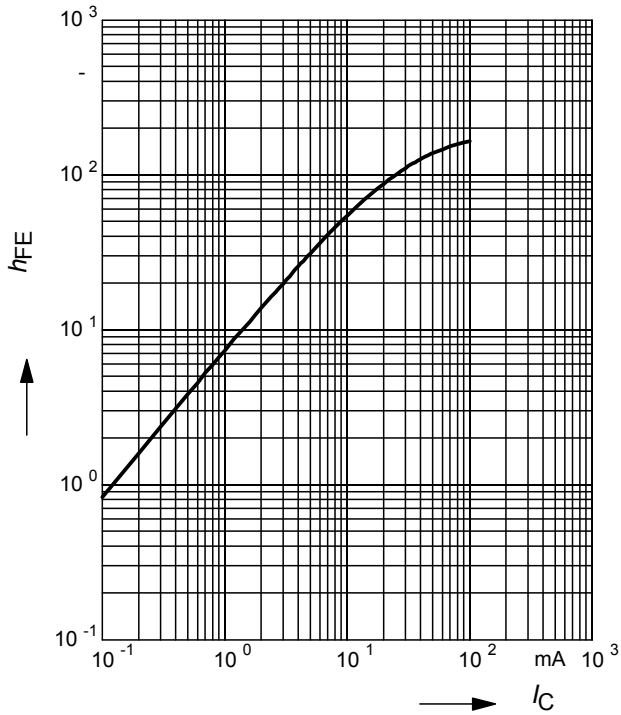
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	1.61	mA
DC current gain 1) $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{FE}$	20	-	-	-
Collector-emitter saturation voltage1) $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.8	-	1.5	
Input on Voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	1	-	2.5	
Input resistor	$R_1$	3.2	4.7	6.2	k $\Omega$
Resistor ratio	$R_1/R_2$	0.9	1	1.1	-
<b>AC Characteristics</b>					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	140	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

 1) Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**NPN Type**

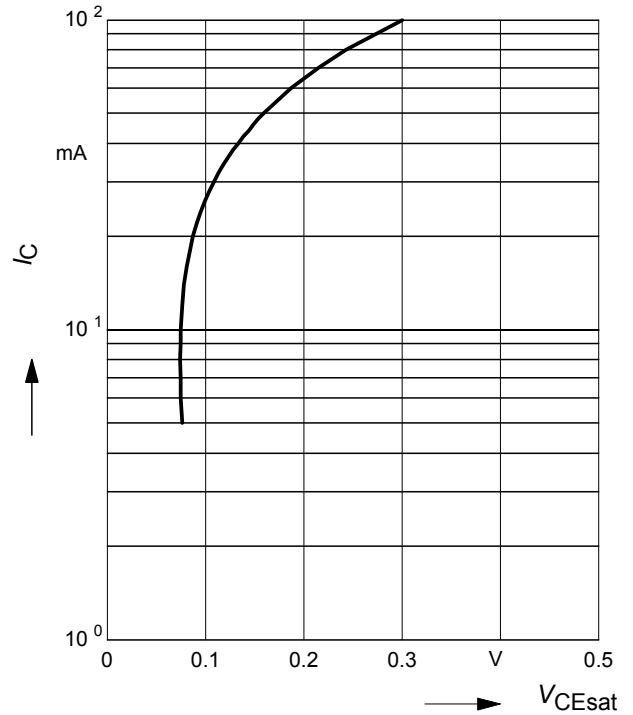
**DC Current Gain**  $h_{FE} = f(I_C)$

$V_{CE} = 5V$  (common emitter configuration)



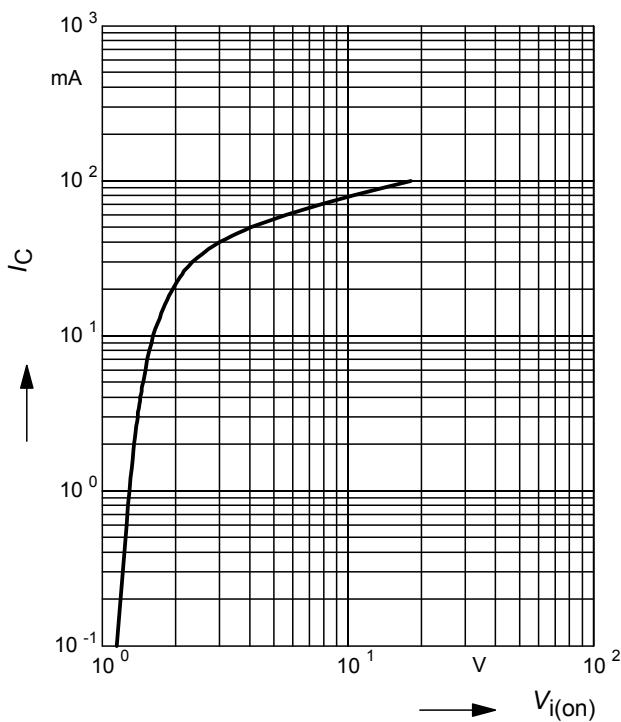
**Collector-Emitter Saturation Voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



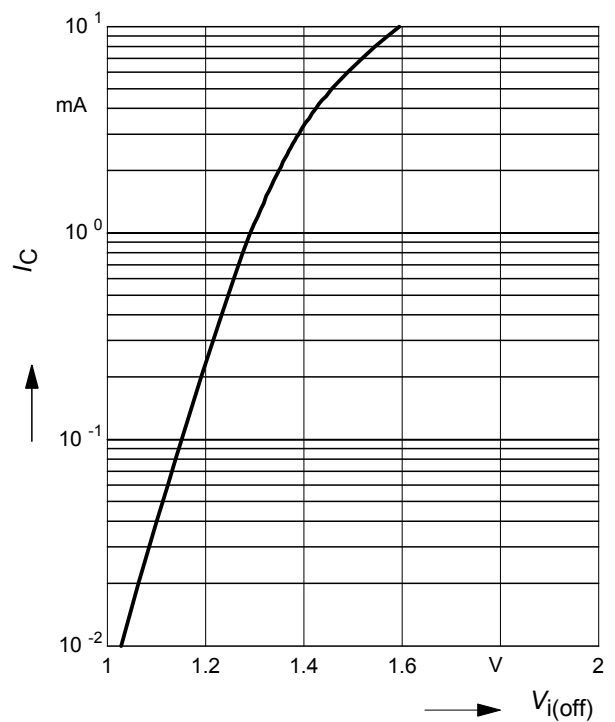
**Input on Voltage**  $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$  (common emitter configuration)



**Input off voltage**  $V_{i(off)} = f(I_C)$

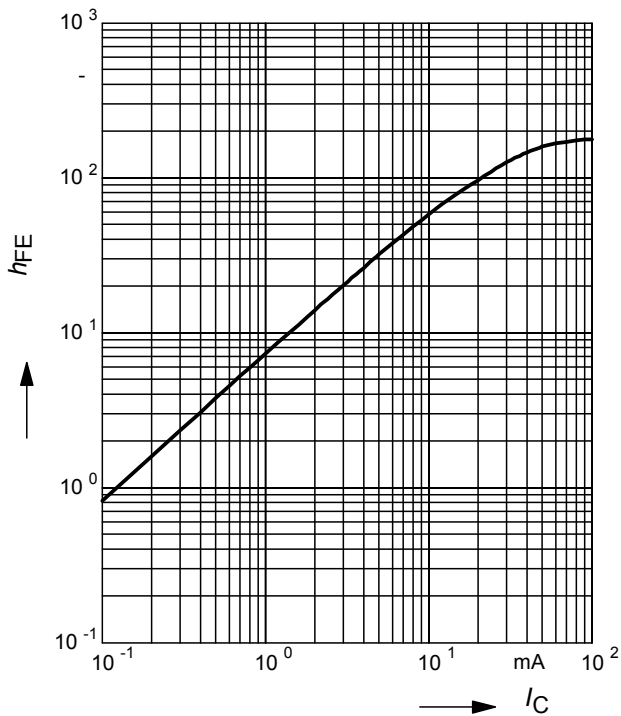
$V_{CE} = 5V$  (common emitter configuration)



**PNP Type**

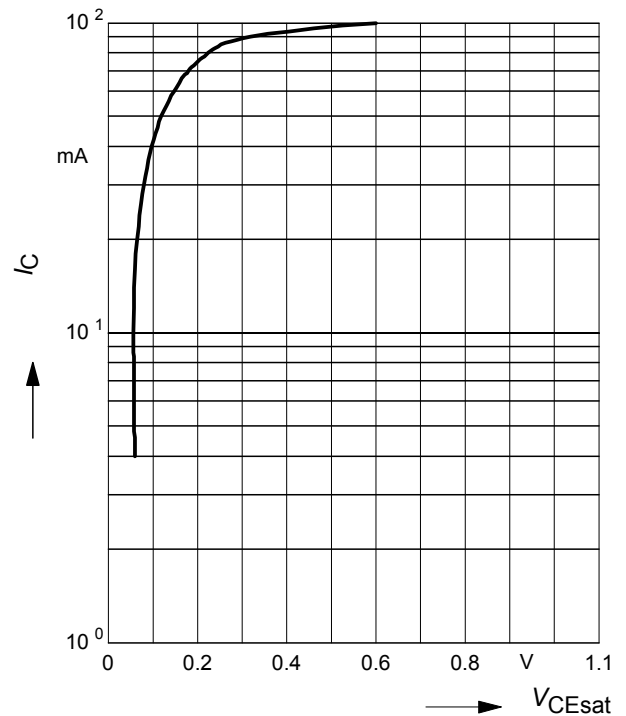
**DC Current Gain**  $h_{FE} = f(I_C)$

$V_{CE} = 5V$  (common emitter configuration)



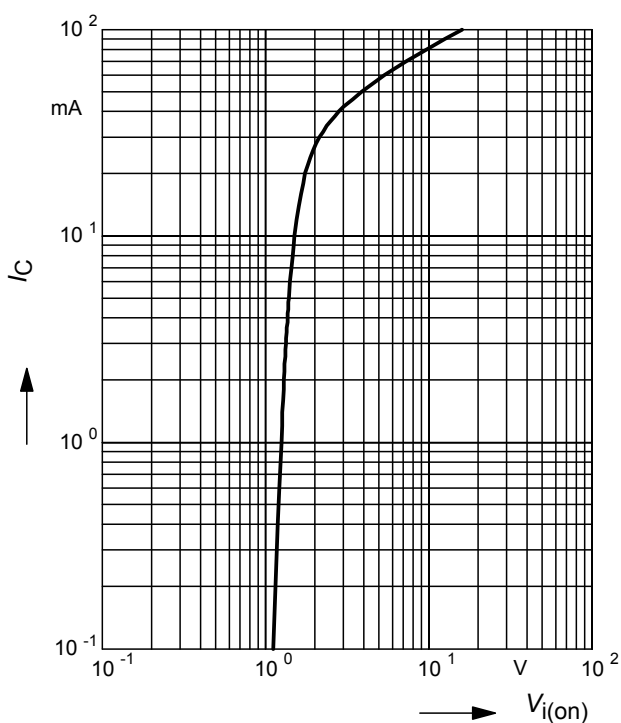
**Collector-Emitter Saturation Voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



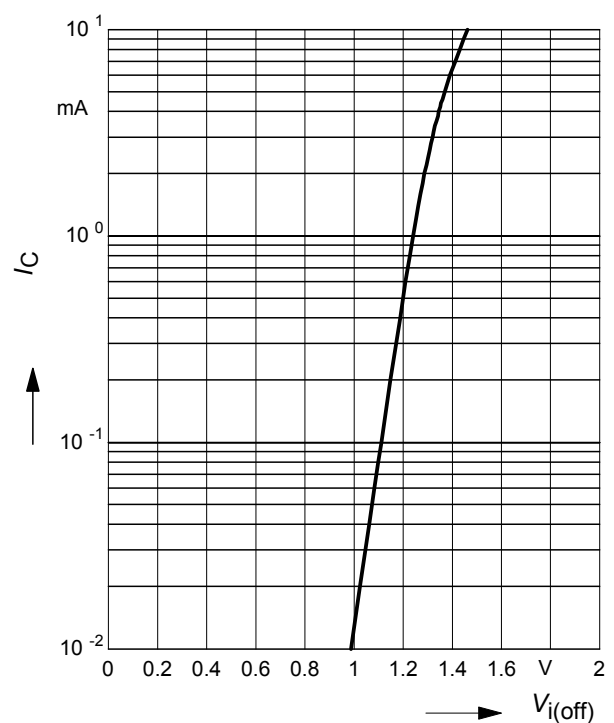
**Input on Voltage**  $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$  (common emitter configuration)

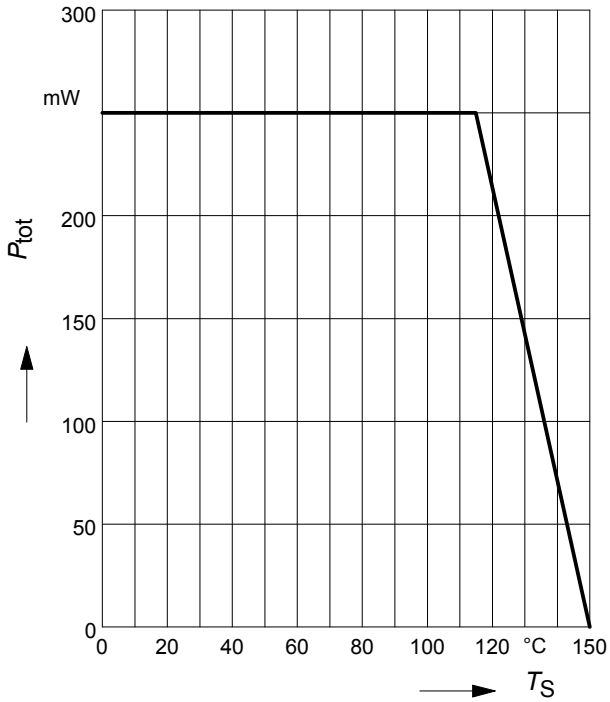


**Input off voltage**  $V_{i(off)} = f(I_C)$

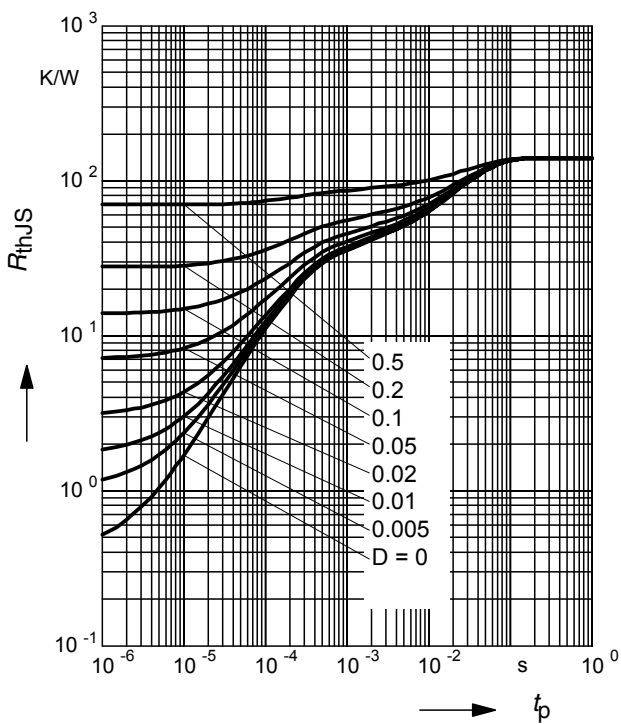
$V_{CE} = 5V$  (common emitter configuration)



**Total power dissipation  $P_{tot} = f(T_S)$**

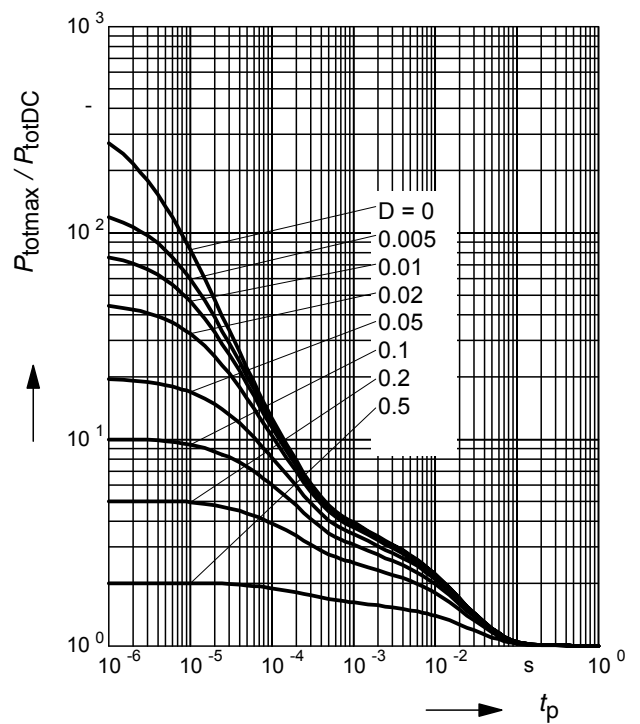


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



**Permissible Pulse Load**

$P_{totmax} / P_{totDC} = f(t_p)$



**Published by Infineon Technologies AG,  
St.-Martin-Strasse 53,  
81669 München**

**© Infineon Technologies AG 2004.  
All Rights Reserved.**

**Attention please!**

The information herein is given to describe certain components and shall not be considered as a guarantee of characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

**Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

**Warnings**

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.